

TRADEMARK ASSIGNMENT

Electronic Version v1.1
 Stylesheet Version v1.1

SUBMISSION TYPE:	NEW ASSIGNMENT
NATURE OF CONVEYANCE:	RELEASE BY SECURED PARTY

CONVEYING PARTY DATA

Name	Formerly	Execution Date	Entity Type
SILICON VALLEY BANK		11/16/2012	CORPORATION: DELAWARE

RECEIVING PARTY DATA

Name:	SHOCKING TECHNOLOGIES, INC.
Street Address:	5870 HELLYER AVENUE
City:	SAN JOSE
State/Country:	CALIFORNIA
Postal Code:	95138
Entity Type:	CORPORATION: DELAWARE

PROPERTY NUMBERS Total: 6

Property Type	Number	Word Mark
Registration Number:	4070821	XSTATIC
Registration Number:	4077363	XSEED
Registration Number:	4077364	SHOCKING TECHNOLOGIES
Registration Number:	4084150	SHOCKING TECHNOLOGIES
Serial Number:	77208973	GLOBAL ESD PROTECTION
Serial Number:	77208991	CATCH THE SPARK

CORRESPONDENCE DATA

Fax Number: 2138925163
Correspondence will be sent to the e-mail address first; if that is unsuccessful, it will be sent via US Mail.

Phone: 2138924000
 Email: lrizzo@milbank.com
 Correspondent Name: Milbank, Tweed, Hadley & McCloy LLP
 Address Line 1: 601 South Figueroa Street, Suite 3000
 Address Line 4: Los Angeles, CALIFORNIA 90017

CH \$165.00 4070821

ATTORNEY DOCKET NUMBER:	40855.00000
NAME OF SUBMITTER:	Chris L. Holm
Signature:	/Chris L. Holm/
Date:	11/20/2012
Total Attachments: 6 source=Release of IP Security#page1.tif source=Release of IP Security#page2.tif source=Release of IP Security#page3.tif source=Release of IP Security#page4.tif source=Release of IP Security#page5.tif source=Release of IP Security#page6.tif	

**RELEASE OF SECURITY INTEREST
INTELLECTUAL PROPERTY COLLATERAL ASSIGNMENT**

This RELEASE OF SECURITY INTEREST, dated November 16, 2012 (“Agreement”), is made and entered into among SILICON VALLEY BANK (the “Secured Party”) and SHOCKING TECHNOLOGIES, INC, a Delaware Corporation (“STI”).

WHEREAS, the Secured Party and STI have entered that certain loan agreement, dated July 21, 2010 (as amended, restated, supplemented and/or otherwise modified from time to time, the “Loan Agreement”);

WHEREAS, to secure its obligations under the Loan Agreement, STI entered into that certain Intellectual Property Security Agreement, dated July 21, 2010 (the “Security Assignment”), wherein it assigned certain collateral to the Secured Party, including the Intellectual Property listed in **Schedule A** attached hereto (collectively, the “STI IP”); and

WHEREAS, all obligations under the Loan Agreement have been satisfied and all liens under the Security Agreement have been terminated, and the Secured Party wishes to terminate and release all security interests, pledges, assignments, mortgages and liens of record granted to it in the STI IP under the Security Agreement.

NOW, THEREFORE, in consideration of the mutual covenants and agreements contained herein and other good and valuable consideration, receipt of which is hereby acknowledged, the Secured Party and STI agree as follows:


1. Release. The Secured Party hereby discharges, terminates and releases all security interests, pledges, assignments, mortgages and liens granted to it (collectively, “Security Interests”) in the STI IP under the Security Agreement, and agrees that all of the Security Interests in the STI IP are hereby discharged, terminated and released and hereby transfers and assigns to STI any and all right, title and interest that Secured Party may have obtained in, to and under the STI IP under the Security Agreement.

2. Perfection. Each of STI and the Secured Party hereby authorizes the Director of the United States Patent and Trademark Office to record this Agreement to reflect the release of Security Interests and reassignment of any interests with respect to the STI IP.

[REMAINDER OF PAGE INTENTIONALLY LEFT BLANK]

IN WITNESS WHEREOF, the parties have executed this Release of Security Interest as of the date first above-mentioned.

SILICON VALLEY BANK,
as Secured Party

By: 
Name: Bellet Eliasnia
Title: Advisor III

SHOCKING TECHNOLOGIES INC,
as STI

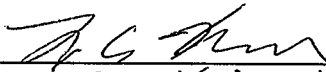
By: _____
Name: _____
Title: _____

IN WITNESS WHEREOF, the parties have executed this Release of Security Interest as of the date first above-mentioned.

SILICON VALLEY BANK,
as Secured Party

By: _____
Name: _____
Title: _____

SHOCKING TECHNOLOGIES INC,
as STI

By: 
Name: Alex Kasow
Title: President & CEO

[Signature Page to IP Release]

#4840-3840-5137

TRADEMARK
REEL: 004904 FRAME: 0868

Schedule A

Trademark	Class(es)	Reg. No. (App. No.)	Reg. Date (App. Date)
Xstatic	17, 42	4070821 (77/208936)	12/13/2011 (6/18/2007)
Xseed	9, 17, 42	4077363 (77/208939)	12/27/2011 (6/18/2007)
Shocking Technologies	9, 17, 42, 45	4077364 (77/208968)	12/27/2011 (6/18/2007)
Global ESD Protection	9, 17, 42	N/A (77/208973)	N/A (6/18/2007)
Shocking Technologies	9, 17, 42, 45	4084150 (77/208985)	1/10/2012 (6/18/2007)
Catch the Spark	9, 17, 42	N/A (77/208991)	N/A (6/18/2007)

Patent Title	Patent No.	Issue Date
System and Method for Including Protective Voltage Switchable Dielectric Material in the Design or Stimulation of Substrate Devices	7793236	9/7/2010
Device Applications for Voltage Switchable Dielectric Material Having High Aspect Ratio Particles	7695644	4/13/2010
Light-Emitting Device Using Voltage Switchable Dielectric Material	7825491	11/2/2010
Current Carrying Structure Using Voltage Switchable Dielectric Material	6797145	9/28/2004
Methods for Fabricating Current-Carrying Structures Using Voltage Switchable Dielectric Materials	7446030	11/4/2008
Formulations for Voltage Switchable Dielectric Material Having a Stepped Voltage Response and Methods for Making the Same	7872251	1/18/2011
Semiconductor Devices Including Voltage Switchable Materials for Over-Voltage Protection	7923844	4/12/2011
Method for Electroplating a Substrate	7968010	6/28/2011
Substrate Device or Package Using Embedded Layer of Voltage Switchable Dielectric Material in a Vertical Switching Configuration	8203421	6/19/2012
Voltage Switchable Dielectric Material Having Bonded Particle Constituents	8206614	6/26/2012

Patent Application Title	Patent App No.	Filing Date
Wireless Communication Device Using Voltage Switchable Dielectric Material	11562222	11/21/2006
Voltage Switchable Dielectric Material Having Conductive or Semi-Conductive Organic Material	11829946	7/29/2007
Voltage Switchable Dielectric Material Having High Aspect Ratio Particles	11829948	7/29/2007
Device Applications For Voltage Switchable Dielectric Material Having Conductive or Semi-Conductive Organic Material	11829951	7/29/2007
Technique for Plating Substrate Devices Using Voltage Switchable Dielectric Material and Light Assistance	11860522	9/24/2007
Voltage Switchable Dielectric Material Having High Aspect Ratio Particles	12193603	8/18/2008
Methods for Fabricating Current-Carrying Structures Using Voltage Switchable Dielectric Materials	12284790	9/24/2008
Voltage Switchable Dielectric Material With Superior Physical Properties for Structural Applications	12370589	2/12/2009
Voltage Switchable Dielectric Material With Low Band Gap Particles	12407346	3/19/2009
Core Layer Structure Having Voltage Switchable Dielectric Material	12541963	8/16/2009
Voltage Switchable Dielectric Material Containing Boron Compound	12561195	9/16/2009
Voltage Switchable Dielectric Material Containing Conductive Core Shelled Particles	12571318	9/30/2009
Geometric and Electric Field Considerations for Including Transient Protective Material in Substrate Devices	12607952	10/28/2009
Metal Deposition	12608297	10/29/2009
Metal Deposition	12608301	10/29/2009
Metal Deposition	12608309	10/29/2009
Metal Deposition	12608315	10/29/2009
Metal Deposition	12608326	10/29/2009
Voltage Switchable Dielectric Material Containing Conductor-on-Conductor Core Shelled Particles	12638360	12/15/2009
Voltage Switchable Dielectric Material Containing Insulative and/or Low-Dielectric Core Shell Particles	12638632	12/15/2009
Voltage Switchable Dielectric Material Incorporating P and N Type Material	12642799	12/19/2009
Voltage Switchable Dielectric Composition Using Binder With Enhanced Electron Mobility at High Electric Fields	12692573	1/22/2010
Substrates Having Voltage Switchable Dielectric Materials	12694702	1/27/2010
Voltage Switchable Dielectric Material Having a Quantity of Carbon Nanotubes Distributed Therein	12714354	2/26/2010
Method for Creating Voltage Switchable Dielectric	12714358	2/26/2010

Material		
Components Having Voltage Switchable Dielectric Materials	12731557	3/25/2010

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RECORDED: 11/20/2012

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